## BA591WS

## BAND SWITCHING DIODE

## Features

- Very small plastic SMD package
- Low diode capacitance
- Low diode forward resistance
- Small inductance

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Top View
Marking Code: "WL"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Continuous Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 35 | V |
| Continuous Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 100 | mA |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | 500 | mW |
| Operating Junction Temperature Range | $\mathrm{T}_{\mathrm{J}}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Electrical Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Typ. | Max. | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Forward Voltage <br> at $I_{F}=10 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | - | 1 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | - | 20 | nA |
| Diode Capacitance <br> at $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ <br> at $\mathrm{V}_{\mathrm{R}}=3 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\mathrm{D}}$ | - | 1.05 | pF |
| Diode Forward Resistance <br> at $\mathrm{I}_{\mathrm{F}}=3 \mathrm{~mA}, \mathrm{f}=100 \mathrm{MHz}$ <br> at $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{f}=100 \mathrm{MHz}$ | $\mathrm{r}_{\mathrm{D}}$ | - | 0.9 | 0.7 |
| Reverse Resistance <br> at $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}, \mathrm{f}=100 \mathrm{MHz}$ | $1 / \mathrm{g}_{\mathrm{p}}$ | 100 | - | $\Omega$ |
| Series Inductance | Ls | 2 | - | $\mathrm{n} \Omega$ |


$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$.
Fig. 2 Diode capacitance as a function of reverse voltage; typical values.

$\mathrm{f}=100 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$.
Diode forward resistance as a function of forward current; typical values.

## PACKAGE OUTLINE



| UNIT | A | $\mathrm{b}_{\rho}$ | C | D | E | $\mathrm{H}_{\mathrm{E}}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 1.10 | 0.40 | 0.15 | 1.80 | 1.35 | 2.80 |
|  | 0.80 | 0.25 | 0.00 | 1.60 | 1.15 | 2.30 |

